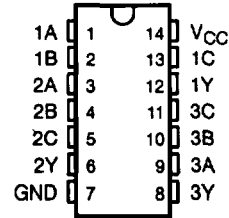


SN74LVC10 TRIPLE 3-INPUT POSITIVE-NAND GATE

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- **EPIC™** (Enhanced-Performance Implanted CMOS) Submicron Process
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at $V_{CC} = 3.3 V, T_A = 25^\circ C$**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at $V_{CC} = 3.3 V, T_A = 25^\circ C$**
- **Inputs Accept Voltages to 5.5 V**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This triple 3-input positive-NAND gate is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC10 performs the Boolean functions $Y = \overline{A \cdot B \cdot C}$ or $Y = \overline{A + B + C}$ in positive logic.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC10 is characterized for operation from $-40^\circ C$ to $85^\circ C$.

FUNCTION TABLE
(each gate)

INPUTS			OUTPUT
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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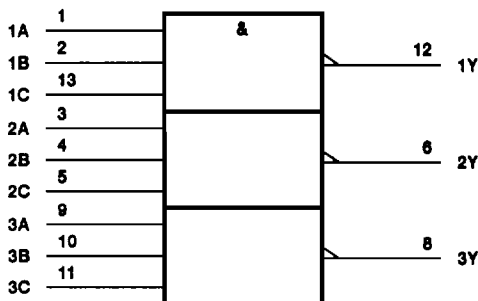
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SN74LVC10

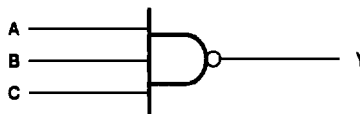
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logic symbol†



logic diagram, each gate (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC}	-0.5 V to 6.5 V
Input voltage range, V_I (see Note 1)	-0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2)	-0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$)	-50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±50 mA
Continuous current through V_{CC} or GND	±100 mA
Maximum power dissipation at $T_A = 55^\circ\text{C}$ (in still air) (see Note 3): D package	1.25 W
DB or PW package	0.5 W
Storage temperature range, T_{stg}	-65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 2. This value is limited to 4.6 V maximum.
 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

		MIN	MAX	UNIT	
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	$V_{CC} = 2.7$ V to 3.6 V		V	
V_{IL}	Low-level input voltage	$V_{CC} = 2.7$ V to 3.6 V		0.8	
V_I	Input voltage	0	5.5	V	
V_O	Output voltage	0	V_{CC}	V	
I_{OH}	High-level output current	$V_{CC} = 2.7$ V	-12	mA	
		$V_{CC} = 3$ V	-24		
I_{OL}	Low-level output current	$V_{CC} = 2.7$ V	12	mA	
		$V_{CC} = 3$ V	24		
T_A	Operating free-air temperature	-40	85	°C	

NOTE 4: Unused inputs must be held high or low to prevent them from floating.



SN74LVC10

TRIPLE 3-INPUT POSITIVE-NAND GATE

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC} †	MIN	TYP‡	MAX	UNIT
V _{OH}	I _{OH} = -100 µA	MIN to MAX	V _{CC} -0.2			V
	I _{OH} = -12 mA	2.7 V	2.2			
	I _{OH} = -24 mA	3 V	2.4			
V _{OL}	I _{OL} = 100 µA	MIN to MAX			0.2	V
	I _{OL} = 12 mA	2.7 V			0.4	
	I _{OL} = 24 mA	3 V			0.55	
I _I	V _I = 5.5 V or GND	3.6 V			±5	µA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	3.6 V			10	µA
ΔI _{CC}	One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	2.7 V to 3.6 V			500	µA
C _I	V _I = V _{CC} or GND	3.3 V	5			pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t _{pd}	A	Y	1	6		7	ns
t _{sk(o)} §			1				ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd} Power dissipation capacitance per gate	C _L = 50 pF, f = 10 MHz	11	pF

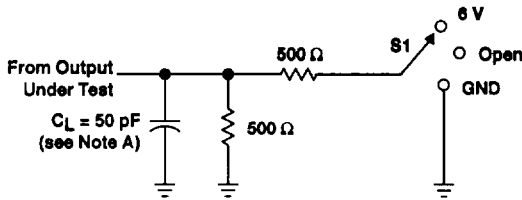


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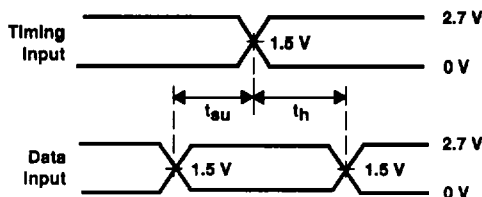
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PARAMETER MEASUREMENT INFORMATION

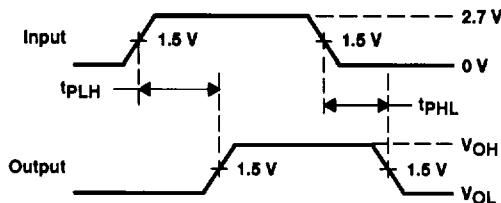
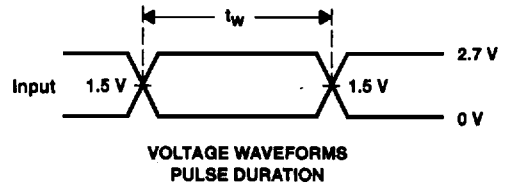


LOAD CIRCUIT

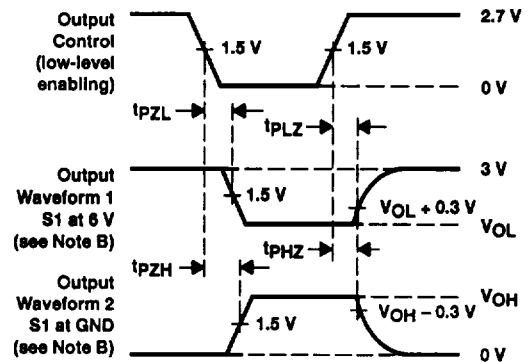
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
 D. The outputs are measured one at a time with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms